/idth (0.5)

(C0.5)

Gate the rest

1: Cathode

4: Collector

2: Anode 3: Emitter

SEC.

Unit: mm

# CNZ1002 (ON1002)

### Photo Interrupter

For contactless SW, object detection

#### Overview

CNZ1002 is an ultraminiature, highly reliable transmissive photosensor in which a high efficiency GaAs infrared light emitting diode chip and a high sensitivity Si phototransistor chip are integrated in a double molded resin package.

#### Features

- Ultraminiature: 4.0 mm × 3.8 mm (height: 5.1 mm)
- Fast response:  $t_r$ ,  $t_f = 35 \ \mu s$  (typ.)
- Highly precise position detection: 0.25 mm
- Gap width: 0.9 mm

### Absolute Maximum Ratings $T_a = 25^{\circ}C$

					-	PISMR104-001 Package
Parameter		Symbol	Rating	Unit		(Note) 1. Tolerance unless otherwise specified is $\pm 0.2$
Input (Light	Reverse voltage	V <sub>R</sub>	6	V		<ul><li>2. ( ) Dimension is reference</li><li>3. * is dimension at the root of leads</li></ul>
emitting diode)	Forward current	I <sub>F</sub>	50	mA		4. Burrs should be less than 0.15 mm
	Power dissipation *1	PD	75	mW		×0'
Output (Photo transistor)	Collector-emitter voltage (Base open)	V <sub>CEO</sub>	35	V		Still
	Emitter-collector voltage (Base open)	V <sub>ECO</sub>	6	V		t late len
	Collector current	I <sub>C</sub>	20	mA	- NT-4-)	
	Collector power dissipation *2	P <sub>C</sub>	75	mW	- Note)	*1 Input power derating ratio is 1.0 mW/°C at $T_a \ge 25^{\circ}C$ .
Temperature	Operating ambient temperature	T <sub>opr</sub>	-25 to +85	°C		*2: Output power derating ratio is 1.0 mW/°C at
	Storage temperature	T <sub>stg</sub>	-40 to +100	°C	K~ .	T. $\geq 25^{\circ}$ C.

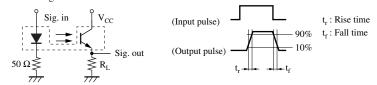
#### $= 25^{\circ}C \pm 3^{\circ}C$ Electrical-Optical Characteristics T<sub>a</sub>

Electrical-Optical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$												
	Parameter	Symbol	Conditions	Min	Тур	Max	Unit					
Input	Forward voltage	V <sub>F</sub>	$I_{\rm F} = 20  {\rm mA}$		1.2	1.4	V					
characteristics	Reverse current	I <sub>R</sub>	$V_R = 3 V$			10	μΑ					
Output	Collector-emitter cutoff current	I <sub>CEO</sub>	$V_{CE} = 20$ V			100	nA					
characteristics	(Base open)	, C										
Transfer	Collector current	J <sub>C</sub>	$V_{CE} = 5 V, I_F = 1.5 mA$	65		480	μΑ					
characteristics	Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_F = 3 \text{ mA}, I_C = 30 \mu \text{A}$			0.4	V					
	Rise time *	t <sub>r</sub>	$V_{CC} = 5 \text{ V}, I_C = 0.1 \text{ mA}$		35		μs					
	Fall time *	t <sub>f</sub>	$R_L = 1000~\Omega$		35		μs					

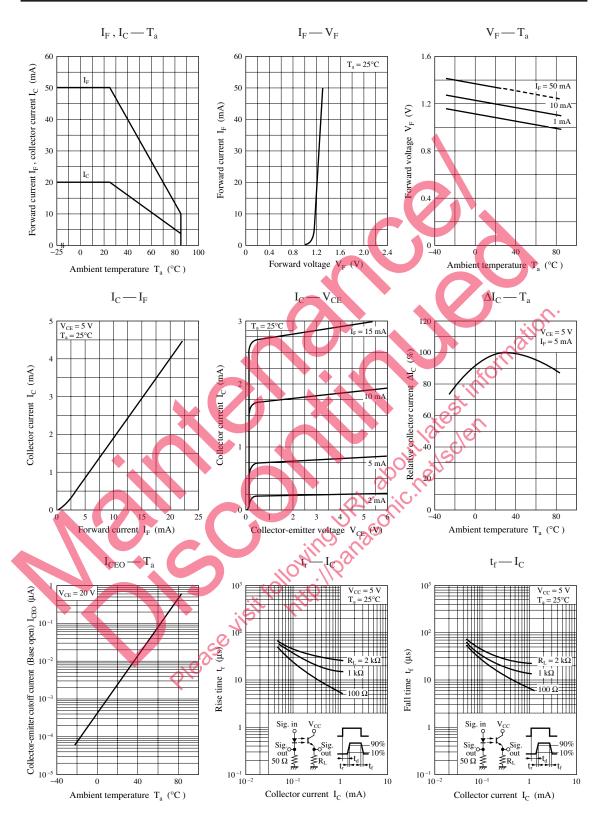
Note) 1. Input and output are practiced by electricity.

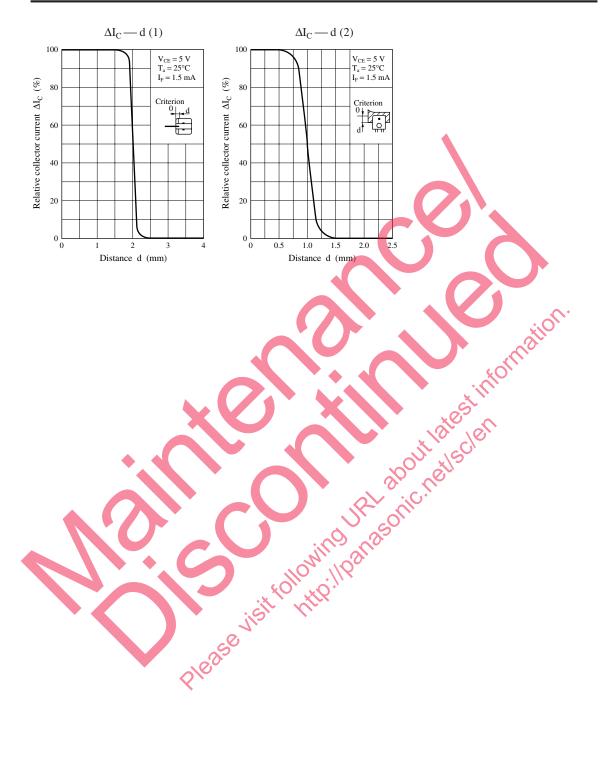
2. This device is designed be disregarded radiation.

3. \*: Switching time measurement circuit



Note) The part number in the parenthesis shows conventional part number.

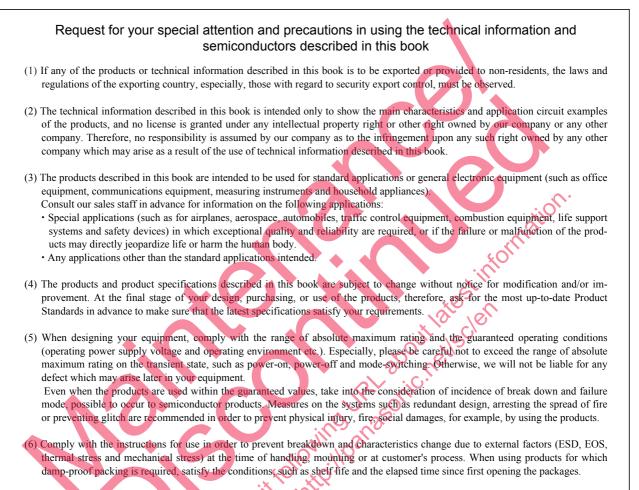




# ▲Caution for Safety

## This product contains Gallium Arsenide (GaAs).

GaAs powder and vapor are hazardous to human health if inhaled or ingested. Do not burn, destroy, cut, cleave off, or chemically dissolve the product. Follow related laws and ordinances for disposal. The product should be excluded from general industrial waste or household garbage.



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